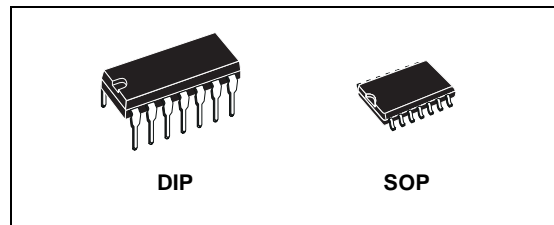


QUAD EXCLUSIVE-OR GATE

- MEDIUM SPEED OPERATION - $t_{PHL} = t_{PLH} = 65\text{ns}$ (TYP.) at $C_L = 50\text{pF}$ and $V_{DD} - V_{SS} = 10\text{V}$
- LOW OUTPUT IMPEDANCE : $500\ \Omega$ (TYP.) at $V_{DD} - V_{SS} = 10\text{V}$
- QUIESCENT CURRENT SPECIFIED UP TO 20V
- 5V, 10V AND 15V PARAMETRIC RATINGS
- INPUT LEAKAGE CURRENT
 $I_l = 100\text{nA}$ (MAX) AT $V_{DD} = 18\text{V}$ $T_A = 25^\circ\text{C}$
- 100% TESTED FOR QUIESCENT CURRENT
- MEETS ALL REQUIREMENTS OF JEDEC JESD13B "STANDARD SPECIFICATIONS FOR DESCRIPTION OF B SERIES CMOS DEVICES"



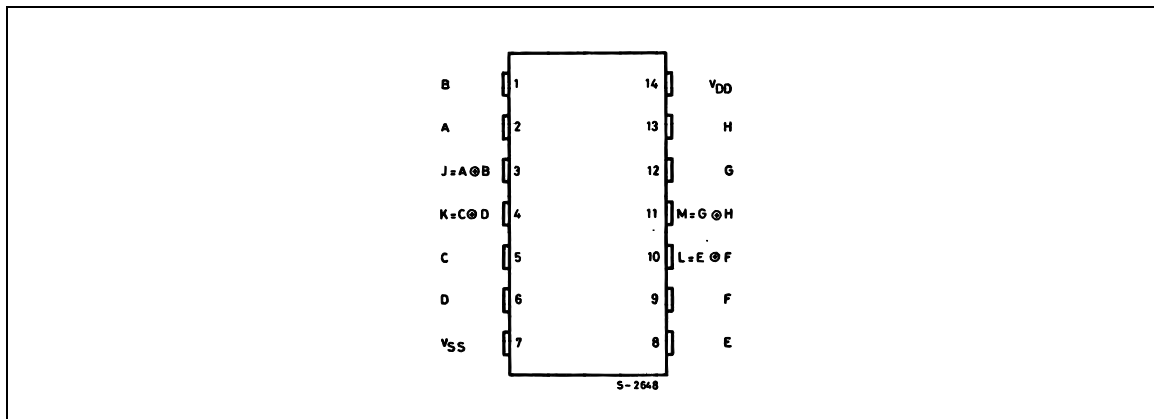
ORDER CODES

PACKAGE	TUBE	T & R
DIP	HCF4030BEY	
SOP	HCF4030BM1	HCF4030M013TR

DESCRIPTION

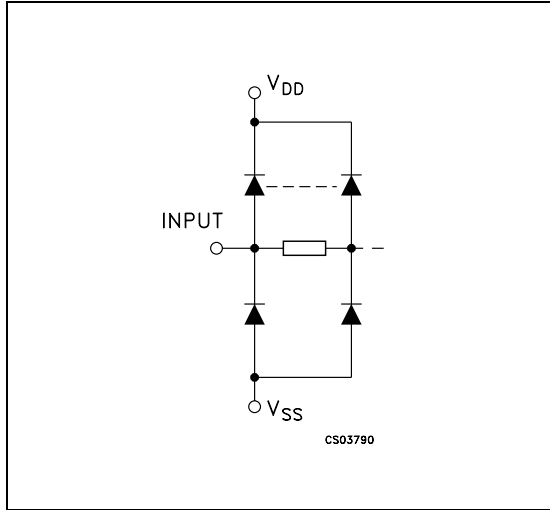
HCF4030B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor technology available in DIP and SOP packages. HCF4030B types consist of four independent exclusive-OR gates integrated on a single monolithic silicon chip. Each exclusive-OR gate consists of four n-channel and four p-channel enhancement-type transistors. All inputs and outputs are protected against electrostatic effects.

PIN CONNECTION



HCF4030B

INPUT EQUIVALENT CIRCUIT



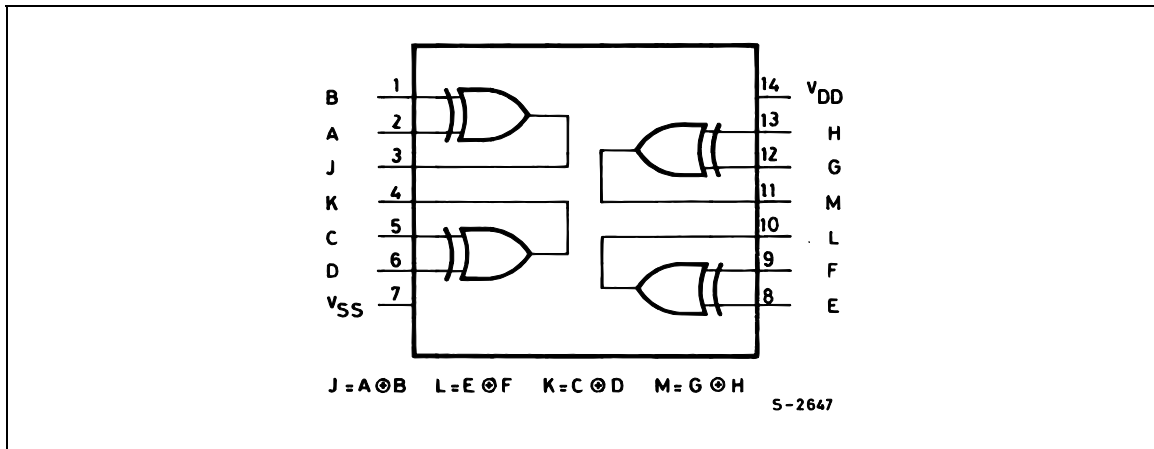
PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
2, 1, 5, 6, 8, 9, 12, 13	A, B, C, D, E, F, G, H	Data Inputs
3, 4, 10, 11	J, K, L, M	Data Outputs
7	V _{SS}	Negative Supply Voltage
14	V _{DD}	Positive Supply Voltage

TRUTH TABLE

IN1	IN2	OUT
L	L	L
L	H	H
H	L	H
H	H	L

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	-0.5 to +22	V
V _I	DC Input Voltage	-0.5 to V _{DD} + 0.5	V
I _I	DC Input Current	± 10	mA
P _D	Power Dissipation per Package	200	mW
	Power Dissipation per Output Transistor	100	mW
T _{op}	Operating Temperature	-55 to +125	°C
T _{stg}	Storage Temperature	-65 to +150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied. All voltage values are referred to V_{SS} pin voltage.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{DD}	Supply Voltage	3 to 20	V
V _I	Input Voltage	0 to V _{DD}	V
T _{op}	Operating Temperature	-55 to 125	°C

DC SPECIFICATIONS

Symbol	Parameter	Test Condition				Value						Unit	
		V _I (V)	V _O (V)	I _{oI} (μA)	V _{DD} (V)	T _A = 25°C			-40 to 85°C		-55 to 125°C		
						Min.	Typ.	Max.	Min.	Max.	Min.		Max.
I _L	Quiescent Current	0/5			5		0.02	4		4		30	μA
		0/10			10		0.02	8		8		60	
		0/15			15		0.02	16		16		120	
		0/20			20		0.04	20		20		600	
V _{OH}	Output High Voltage	0/5		<1	5	4.95			4.95		4.95		V
		0/10		<1	10	9.95			9.95		9.95		
		0/15		<1	15	14.95			14.95		14.95		
V _{OL}	Output Low Voltage	5/0		<1	5		0.05			0.05		0.05	V
		10/0		<1	10		0.05			0.05		0.05	
		15/0		<1	15		0.05			0.05		0.05	
V _{IH}	Input High Voltage		0.5/4.5	<1	5	3.5			3.5		3.5		V
			1/9	<1	10	7			7		7		
			1.5/13.5	<1	15	11			11		11		
V _{IL}	Input Low Voltage		4.5/0.5	<1	5			1.5		1.5		1.5	V
			9/1	<1	10			3		3		3	
			13.5/1.5	<1	15			4		4		4	
I _{OH}	Output Drive Current	0/5	2.5	<1	5	-1.36	-3.2		-1.15		-1.1		mA
		0/5	4.6	<1	5	-0.44	-1		-0.36		-0.36		
		0/10	9.5	<1	10	-1.1	-2.6		-0.9		-0.9		
		0/15	13.5	<1	15	-3.0	-6.8		-2.4		-2.4		
I _{OL}	Output Sink Current	0/5	0.4	<1	5	0.44	1		0.36		0.36		mA
		0/10	0.5	<1	10	1.1	2.6		0.9		0.9		
		0/15	1.5	<1	15	3.0	6.8		2.4		2.4		
I _I	Input Leakage Current	0/18	Any Input		18		±10 ⁻⁵	±0.1		±1		±1	μA
C _I	Input Capacitance		Any Input				5	7.5					pF

The Noise Margin for both "1" and "0" level is: 1V min. with V_{DD}=5V, 2V min. with V_{DD}=10V, 2.5V min. with V_{DD}=15V

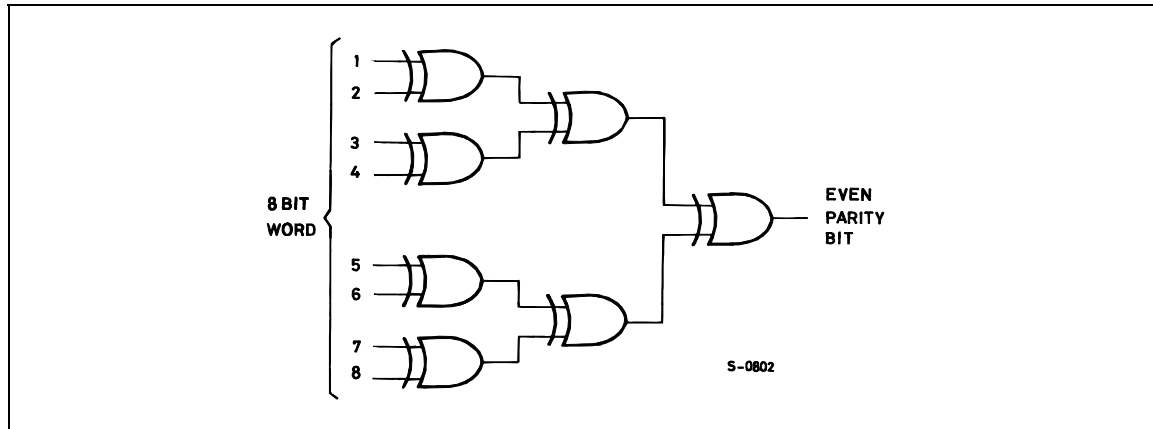
DYNAMIC ELECTRICAL CHARACTERISTICS (T_{amb} = 25°C, C_L = 50pF, R_L = 200KΩ, t_r = t_f = 20 ns)

Symbol	Parameter	Test Condition		Value (*)			Unit
		V _{DD} (V)		Min.	Typ.	Max.	
t _{PLH} t _{PHL}	Propagation Delay Time	5			140	280	ns
		10			65	130	
		15			50	100	
t _{TLH} t _{THL}	Output Transition Time	5			100	200	ns
		10			50	100	
		15			40	80	

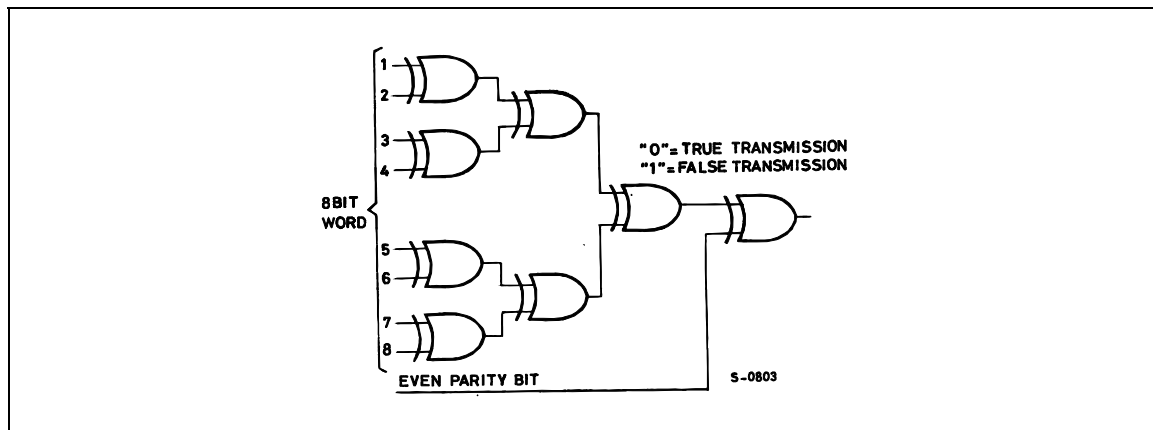


HCF4030B

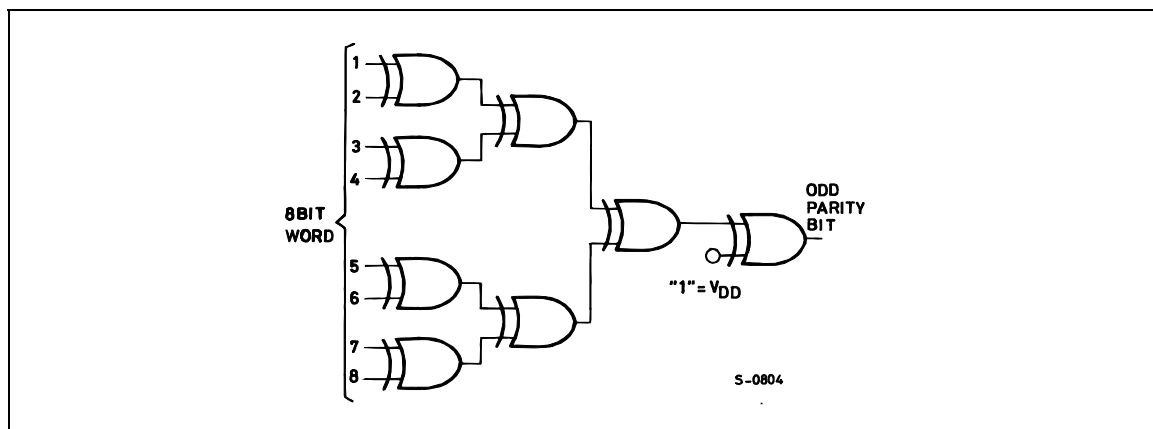
TYPICAL APPLICATION : EVEN PARITY-BIT GENERATOR



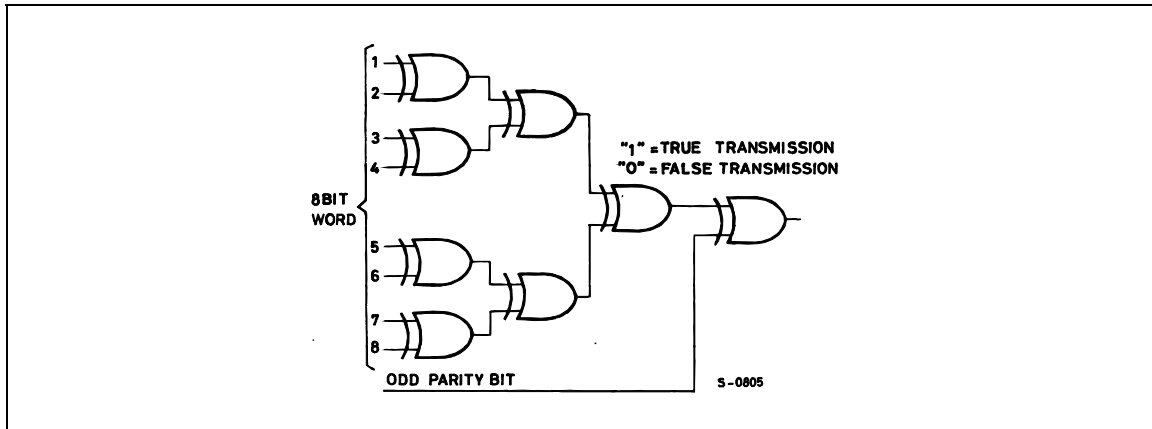
TYPICAL APPLICATION : EVEN PARITY-CHECKER



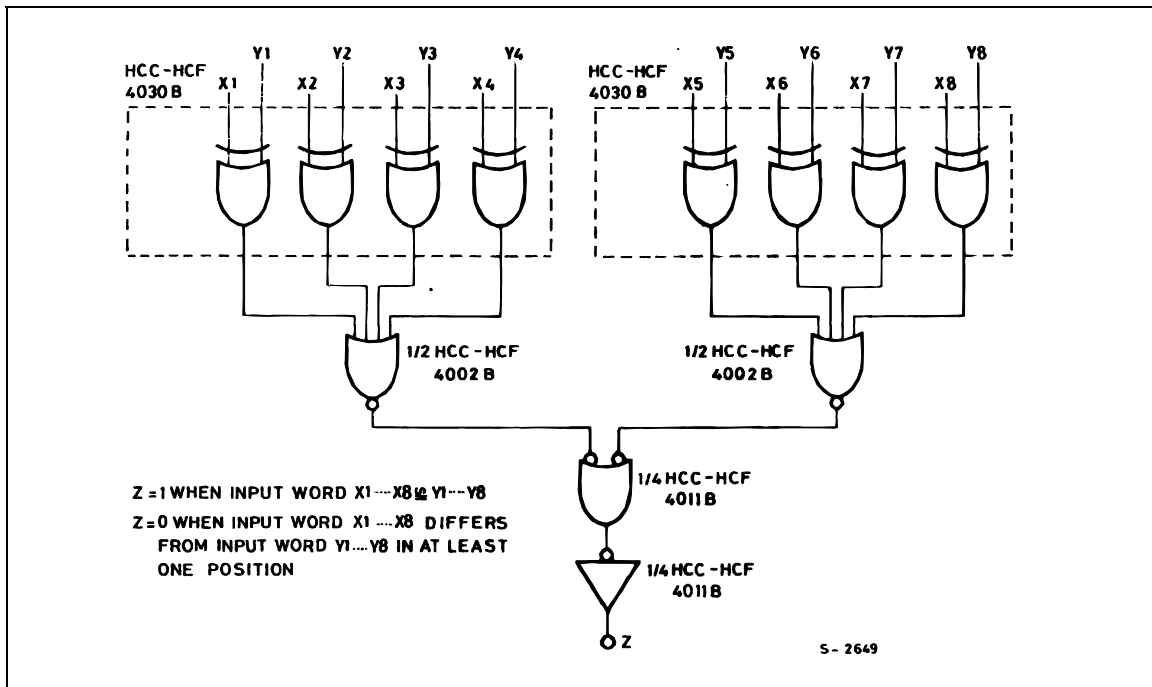
TYPICAL APPLICATION : ODD-PARITY-BIT GENERATOR

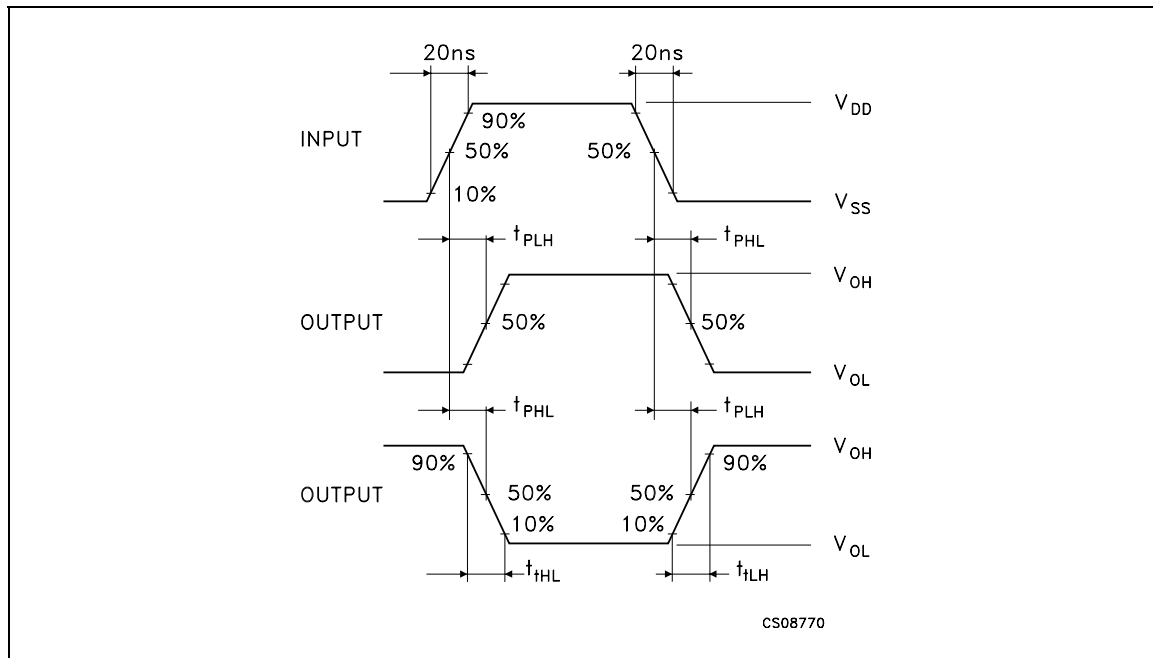


TYPICAL APPLICATION : ODD-PARITY-CHECKER



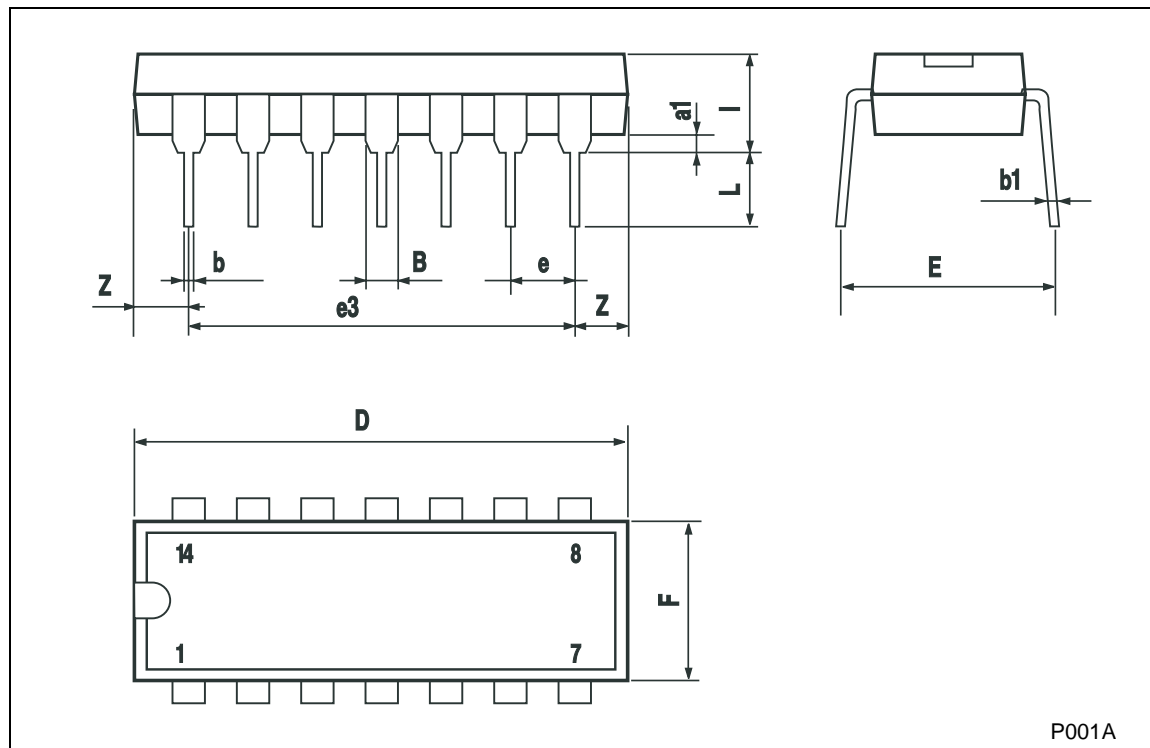
TYPICAL APPLICATION : 8-BIT COMPARATOR



WAVEFORM : PROPAGATION DELAY TIMES ($f=1\text{MHz}$; 50% duty cycle)

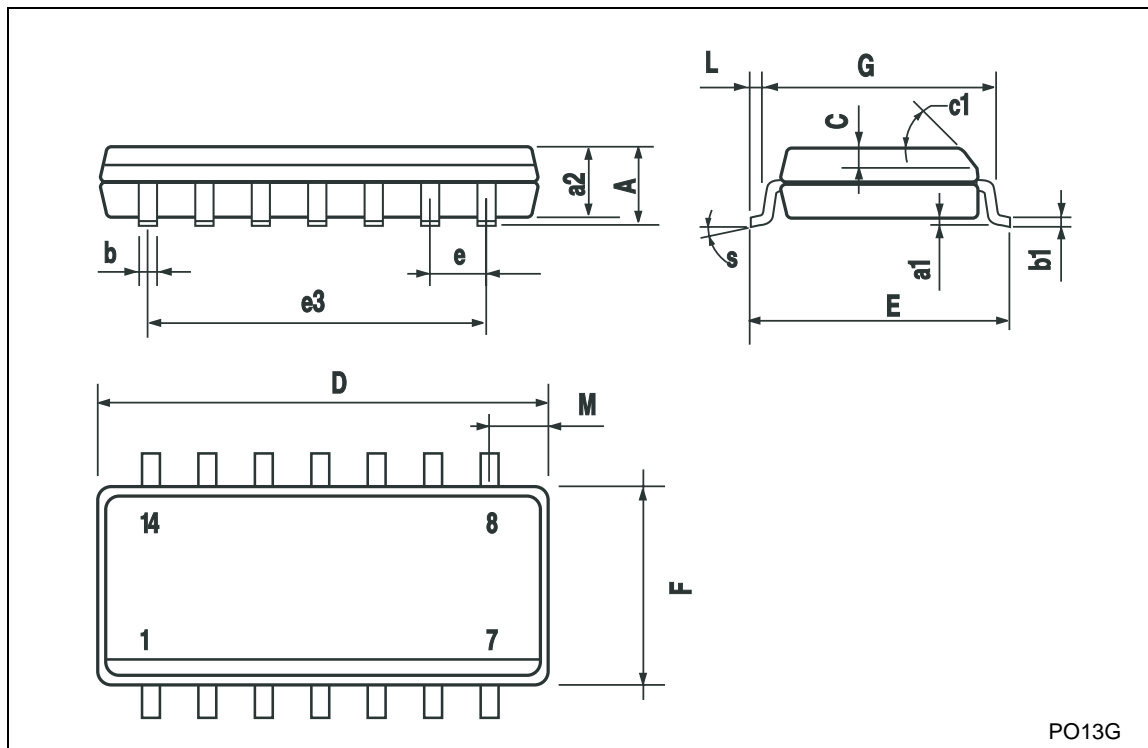
Plastic DIP-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	1.39		1.65	0.055		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		15.24			0.600	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z	1.27		2.54	0.050		0.100



SO-14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



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